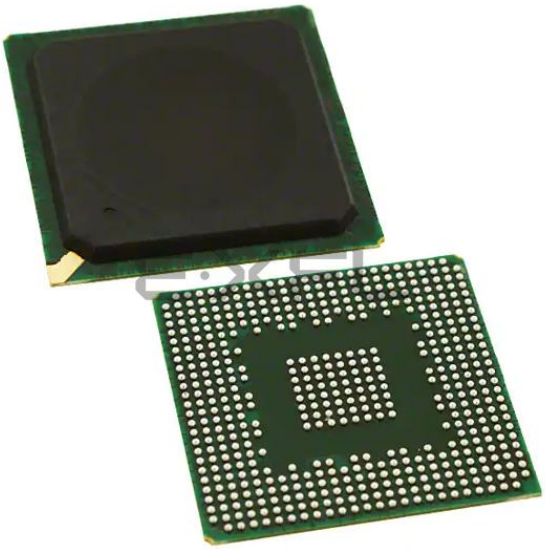
NXP USA Inc. - MPC8313EVRAFFC Datasheet



Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Security; SEC 2.2
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	516-BBGA Exposed Pad
Supplier Device Package	516-TEPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8313evraffc

1 Overview

The MPC8313E incorporates the e300c3 core, which includes 16 Kbytes of L1 instruction and data caches and on-chip memory management units (MMUs). The MPC8313E has interfaces to dual enhanced three-speed 10/100/1000 Mbps Ethernet controllers, a DDR1/DDR2 SDRAM memory controller, an enhanced local bus controller, a 32-bit PCI controller, a dedicated security engine, a USB 2.0 dual-role controller and an on-chip high-speed PHY, a programmable interrupt controller, dual I^{2}C controllers, a 4-channel DMA controller, and a general-purpose I/O port. This figure shows a block diagram of the MPC8313E.

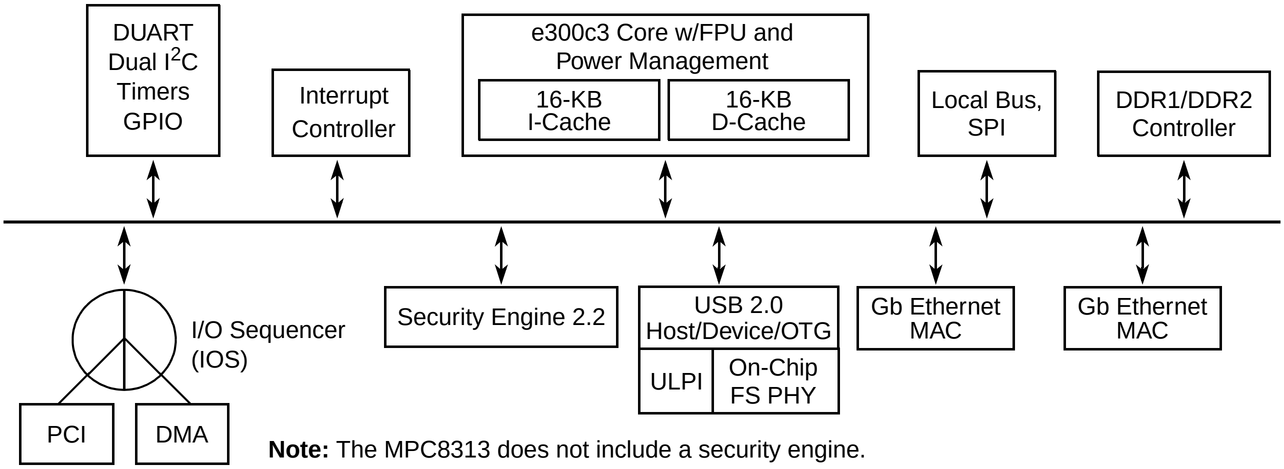


Figure 1. MPC8313E Block Diagram

The MPC8313E security engine (SEC 2.2) allows CPU-intensive cryptographic operations to be offloaded from the main CPU core. The security-processing accelerator provides hardware acceleration for the DES, 3DES, AES, SHA-1, and MD-5 algorithms.

1.1 MPC8313E Features

The following features are supported in the MPC8313E:

- Embedded PowerPC™ e300 processor core built on Power Architecture™ technology; operates at up to 333 MHz.
- High-performance, low-power, and cost-effective host processor
- DDR1/DDR2 memory controller—one 16-/32-bit interface at up to 333 MHz supporting both DDR1 and DDR2
- 16-Kbyte instruction cache and 16-Kbyte data cache, a floating point unit, and two integer units
- Peripheral interfaces such as 32-bit PCI interface with up to 66-MHz operation, 16-bit enhanced local bus interface with up to 66-MHz operation, and USB 2.0 (high speed) with an on-chip PHY.
- Security engine provides acceleration for control and data plane security protocols
- Power management controller for low-power consumption
- High degree of software compatibility with previous-generation PowerQUICC processor-based designs for backward compatibility and easier software migration

1.10 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) allows the MPC8313E to exchange data between other PowerQUICC family chips, Ethernet PHYs for configuration, and peripheral devices such as EEPROMs, real-time clocks, A/D converters, and ISDN devices.

The SPI is a full-duplex, synchronous, character-oriented channel that supports a four-wire interface (receive, transmit, clock, and slave select). The SPI block consists of transmitter and receiver sections, an independent baud-rate generator, and a control unit.

1.11 DMA Controller, Dual I^{2}C, DUART, Local Bus Controller, and Timers

The MPC8313E provides an integrated four-channel DMA controller with the following features:

- Allows chaining (both extended and direct) through local memory-mapped chain descriptors (accessible by local masters)
- Supports misaligned transfers

There are two I^{2}C controllers. These synchronous, multi-master buses can be connected to additional devices for expansion and system development.

The DUART supports full-duplex operation and is compatible with the PC16450 and PC16550 programming models. The 16-byte FIFOs are supported for both the transmitter and the receiver.

The MPC8313E local bus controller (LBC) port allows connections with a wide variety of external DSPs and ASICs. Three separate state machines share the same external pins and can be programmed separately to access different types of devices. The general-purpose chip select machine (GPCM) controls accesses to asynchronous devices using a simple handshake protocol. The three user programmable machines (UPMs) can be programmed to interface to synchronous devices or custom ASIC interfaces. Each chip select can be configured so that the associated chip interface can be controlled by the GPCM or UPM controller. The FCM provides a glueless interface to parallel-bus NAND Flash E2PROM devices. The FCM contains three basic configuration register groups—BR*n*, OR*n*, and FMR. Both may exist in the same system. The local bus can operate at up to 66 MHz.

The MPC8313E system timers include the following features: periodic interrupt timer, real time clock, software watchdog timer, and two general-purpose timer blocks.

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8313E. The MPC8313E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value[1]	Unit	Current Requirement
Core supply voltage	V_{DD}	1.0 V ± 50 mV	V	469 mA
Internal core logic constant power	V_{DDC}	1.0 V ± 50 mV	V	377 mA
SerDes internal digital power	$XCOREV_{DD}$	1.0	V	170 mA
SerDes internal digital ground	$XCOREV_{SS}$	0.0	V	—
SerDes I/O digital power	$XPADV_{DD}$	1.0	V	10 mA
SerDes I/O digital ground	$XPADV_{SS}$	0.0	V	—
SerDes analog power for PLL	$SDAV_{DD}$	1.0 V ± 50 mV	V	10 mA
SerDes analog ground for PLL	$SDAV_{SS}$	0.0	V	—
Dedicated 3.3 V analog power for USB PLL	USB_PLL_PWR3	3.3 V ± 300 mV	V	2–3 mA
Dedicated 1.0 V analog power for USB PLL	USB_PLL_PWR1	1.0 V ± 50 mV	V	2–3 mA
Dedicated analog ground for USB PLL	USB_PLL_GND	0.0	V	—
Dedicated USB power for USB bias circuit	USB_VDDA_BIAS	3.3 V ± 300 mV	V	4–5 mA
Dedicated USB ground for USB bias circuit	USB_VSSA_BIAS	0.0	V	—
Dedicated power for USB transceiver	USB_VDDA	3.3 V ± 300 mV	V	75 mA
Dedicated ground for USB transceiver	USB_VSSA	0.0	V	—
Analog power for e300 core APLL	AV_{DD1} [6]	1.0 V ± 50 mV	V	2–3 mA
Analog power for system APLL	AV_{DD2} [6]	1.0 V ± 50 mV	V	2–3 mA
DDR1 DRAM I/O voltage (333 MHz, 32-bit operation)	GV_{DD}	2.5 V ± 125 mV	V	131 mA
DDR2 DRAM I/O voltage (333 MHz, 32-bit operation)	GV_{DD}	1.8 V ± 80 mV	V	140 mA
Differential reference voltage for DDR controller	MV_{REF}	1/2 DDR supply ($0.49 \times GV_{DD}$ to $0.51 \times GV_{DD}$)	V	—
Standard I/O voltage	NV_{DD}	3.3 V ± 300 mV[2]	V	74 mA
eTSEC2 I/O supply	LV_{DDA}	2.5 V ± 125 mV/ 3.3 V ± 300 mV	V	22 mA
eTSEC1/USB DR I/O supply	LV_{DDB}	2.5 V ± 125 mV/ 3.3 V ± 300 mV	V	44 mA
Supply for eLBC IOs	LV_{DD}	3.3 V ± 300 mV	V	16 mA
Analog and digital ground	V_{SS}	0.0	V	—
Junction temperature range	T_A/T_J [3]	0 to 105	°C	

Table 3. Output Drive Capability (continued)

Driver Type	Output Impedance (Ω)	Supply Voltage
DDR2 signal	18	GV_{DD} = 1.8 V
DUART, system control, I^2C, JTAG, SPI	42	NV_{DD} = 3.3 V
GPIO signals	42	NV_{DD} = 3.3 V
eTSEC signals	42	LV_{DDA}, LV_{DDB} = 2.5/3.3 V
USB signals	42	LV_{DDB} = 2.5/3.3 V

2.2 Power Sequencing

The MPC8313E does not require the core supply voltage (V_{DD} and V_{DDC}) and I/O supply voltages (GV_{DD}, LV_{DD}, and NV_{DD}) to be applied in any particular order. Note that during power ramp-up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there might be a period of time that all input and output pins are actively driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD} and V_{DDC}) before the I/O voltage (GV_{DD}, LV_{DD}, and NV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V; see Figure 3. Once both the power supplies (I/O voltage and core voltage) are stable, wait for a minimum of 32 clock cycles before negating $\overline{\text{PORESET}}$.

Note that there is no specific power down sequence requirement for the MPC8313E. I/O voltage supplies (GV_{DD}, LV_{DD}, and NV_{DD}) do not have any ordering requirements with respect to one another.

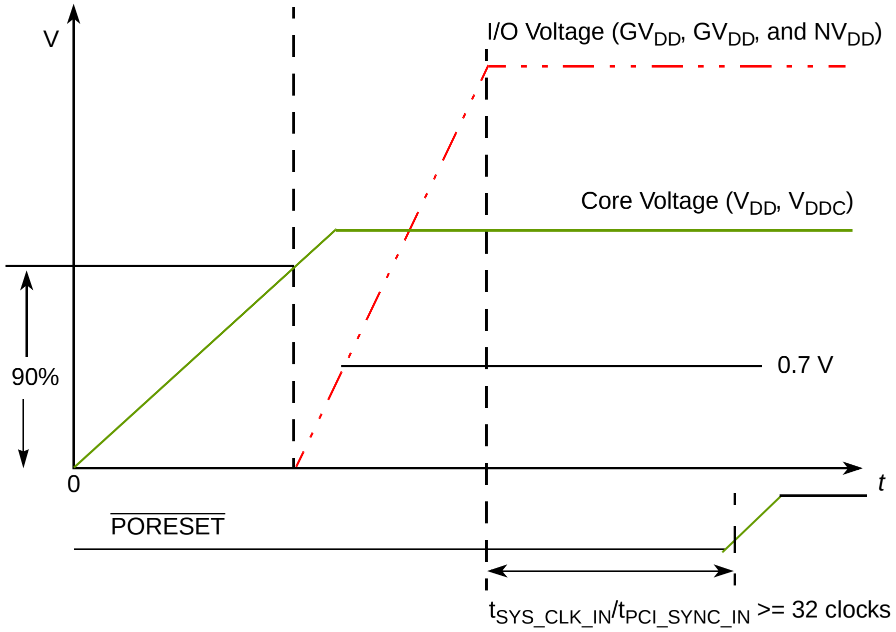


Figure 3. Power-Up Sequencing Example

Table 14. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Note
Output leakage current	I_{OZ}	–9.9	–9.9	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Note:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

This table provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 16. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM when GV_{DD}(typ) = 1.8 V.

Table 17. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 ± 5%.

Parameter	Symbol	Min	Max	Unit	Note
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Rev. 1.0 Silicon

Parameter	Symbol[1]	Min	Max	Unit	Note
MCK[*n*] cycle time, MCK[*n*]/$\overline{\text{MCK}}$[*n*] crossing	t_{MCK}	6	10	ns	2
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHAS}	 2.1 2.5	 — —	ns	3
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHAX}	 2.4 3.15	 — —	ns	3
$\overline{\text{MCS}}$[*n*] output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHCS}	 2.4 3.15	 — —	ns	3
$\overline{\text{MCS}}$[*n*] output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHCX}	 2.4 3.15	 — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ//MDM output setup with respect to MDQS 333 MHz 266 MHz	t_{DDKHDS}, t_{DDKLDS}	 800 900	 — —	ps	5
MDQ//MDM output hold with respect to MDQS 333 MHz 266 MHz	t_{DDKHDX}, t_{DDKLDX}	 900 1100	 — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ//MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual,* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RMII/RGMII/SGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to all the media independent interface (MII), reduced gigabit media independent interface (RGMII), serial gigabit media independent interface (SGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The RGMII and RTBI interfaces are defined for 2.5 V, while the MII interface can be operated at 3.3 V. The RMII and SGMII interfaces can be operated at either 3.3 or 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard reduced pin-count interface for *Gigabit Ethernet Physical Layer Device Specification Version 1.2*a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.5, "Ethernet Management Interface Electrical Characteristics."

8.1.1 TSEC DC Electrical Characteristics

All RGMII, RMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 24 and Table 25. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

NOTE

eTSEC should be interfaced with peripheral operating at same voltage level.

Table 24. MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DDA}/LV_{DDB}	—		2.97	3.63	V
Output high voltage	V_{OH}	$I_{OH} = –4.0$ mA	LV_{DDA} or LV_{DDB} = Min	2.40	LV_{DDA} + 0.3 or LV_{DDB} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DDA} or LV_{DDB} = Min	V_{SS}	0.50	V
Input high voltage	V_{IH}	—	—	2.0	LV_{DDA} + 0.3 or LV_{DDB} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	$V_{IN}{}^1 = LV_{DDA}$ or LV_{DDB}		—	40	μA
Input low current	I_{IL}	$V_{IN}{}^1$ = VSS		–600	—	μA

Note:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Table 25. RGMII/RTBI DC Electrical Characteristics

Parameters	Symbol	Conditions	Min	Max	Unit
Supply voltage 2.5 V	LV_{DDA}/LV_{DDB}	—	2.37	2.63	V

Table 25. RGMII/RTBI DC Electrical Characteristics (continued)

Parameters	Symbol	Conditions		Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DDA} or LV_{DDB} = Min	2.00	LV_{DDA} + 0.3 or LV_{DDB} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DDA} or LV_{DDB} = Min	V_{SS} – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DDA} or LV_{DDB} = Min	1.7	LV_{DDA} + 0.3 or LV_{DDB} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DDA} or LV_{DDB} = Min	–0.3	0.70	V
Input high current	I_{IH}	$V_{IN}^{1} = LV_{DDA}$ or LV_{DDB}		—	10	μA
Input low current	I_{IL}	$V_{IN}^{1} = V_{SS}$		–15	—	μA

Note:

1. Note that the symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 MII, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for MII, RMII, RGMII, and RTBI are presented in this section.

8.2.1 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.1.1 MII Transmit AC Timing Specifications

This table provides the MII transmit AC timing specifications.

Table 26. MII Transmit AC Timing Specifications

At recommended operating conditions with $LV_{DDA}/LV_{DDB}/NV_{DD}$ of 3.3 V ± 0.3 V.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise V_{IL}(min) to V_{IH}(max)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall V_{IH}(max) to V_{IL}(min)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the MII receive AC timing diagram.

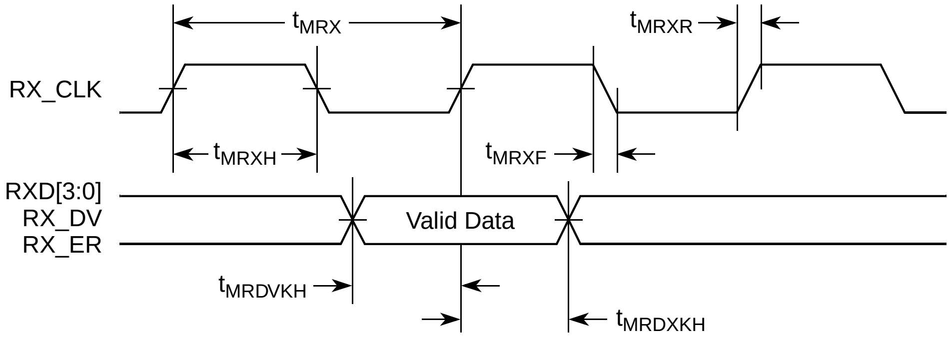


Figure 10. MII Receive AC Timing Diagram RMII AC Timing Specifications

8.2.1.3 RMII Transmit AC Timing Specifications

This table provides the RMII transmit AC timing specifications.

Table 28. RMII Transmit AC Timing Specifications

At recommended operating conditions with NV_{DD} of 3.3 V ± 0.3 V.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$	2	—	10	ns
REF_CLK data clock rise V_{IL}(min) to V_{IH}(max)	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall V_{IH}(max) to V_{IL}(min)	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the RMII transmit AC timing diagram.

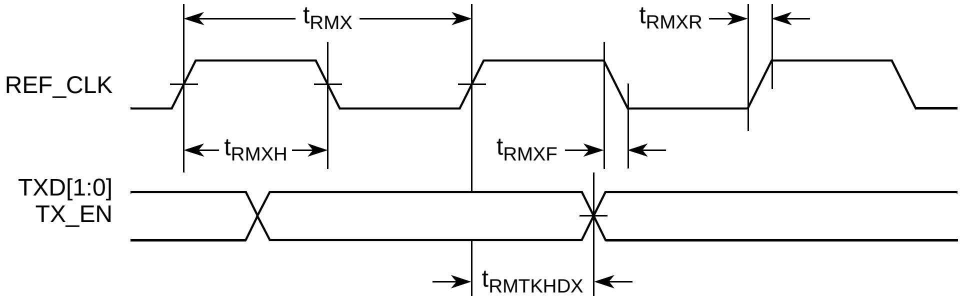


Figure 11. RMII Transmit AC Timing Diagram

This figure shows the RGMII and RTBI AC timing and multiplexing diagrams.

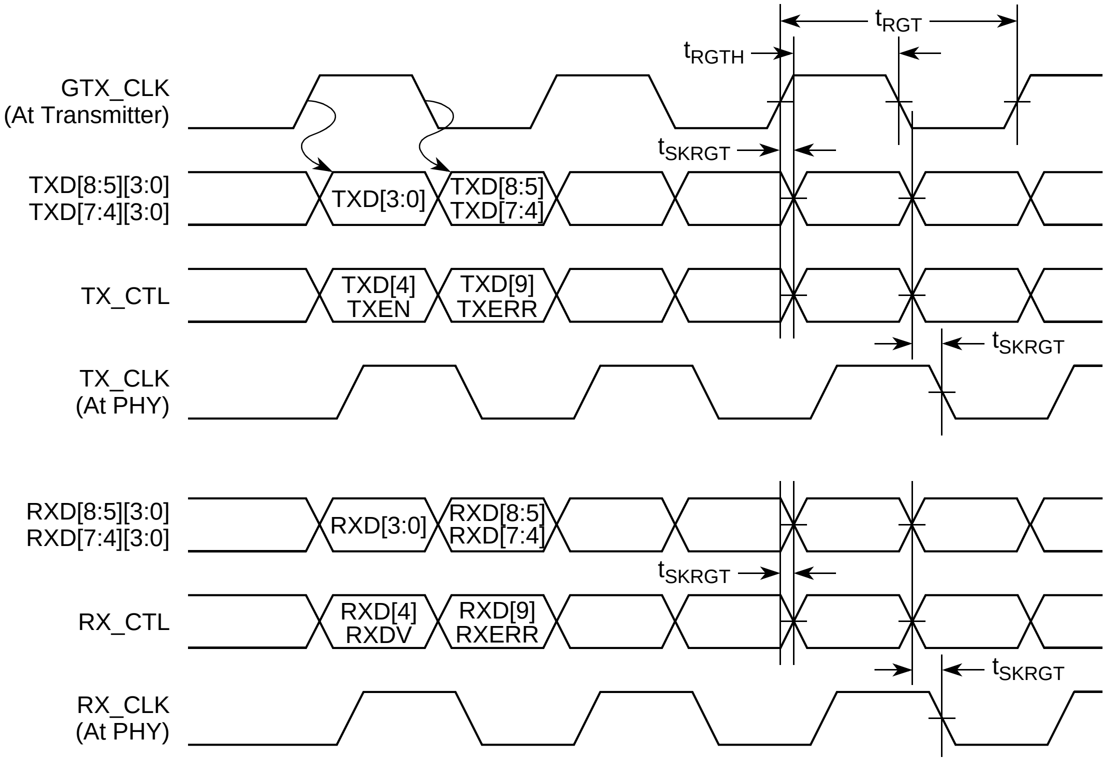


Figure 14. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 SGMII Interface Electrical Characteristics

Each SGMII port features a 4-wire AC-coupled serial link from the dedicated SerDes interface of MPC8313E as shown in Figure 15, where C_{TX} is the external (on board) AC-coupled capacitor. Each output pin of the SerDes transmitter differential pair features a 50-Ω output impedance. Each input of the SerDes receiver differential pair features 50-Ω on-die termination to XCOREVSS. The reference circuit of the SerDes transmitter and receiver is shown in Figure 33.

When an eTSEC port is configured to operate in SGMII mode, the parallel interface’s output signals of this eTSEC port can be left floating. The input signals should be terminated based on the guidelines described in Section 22.5, “Connection Recommendations,” as long as such termination does not violate the desired POR configuration requirement on these pins, if applicable.

When operating in SGMII mode, the TSEC_GTX_CLK125 clock is not required for this port. Instead, the SerDes reference clock is required on SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ pins.

8.3.1 DC Requirements for SGMII SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$

The characteristics and DC requirements of the separate SerDes reference clock are described in Section 9, “High-Speed Serial Interfaces (HSSI).”

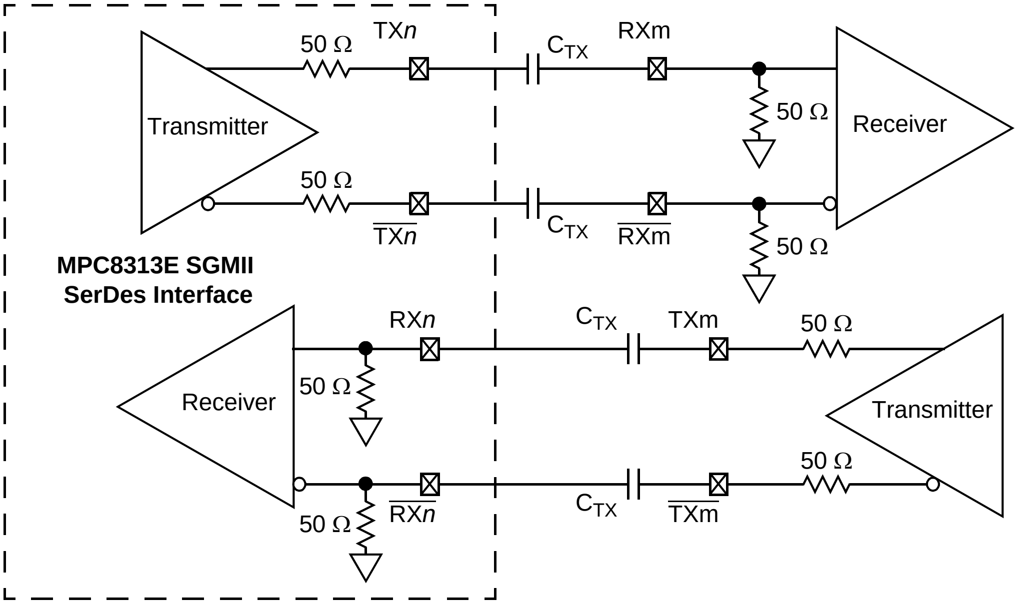


Figure 15. 4-Wire AC-Coupled SGMII Serial Link Connection Example

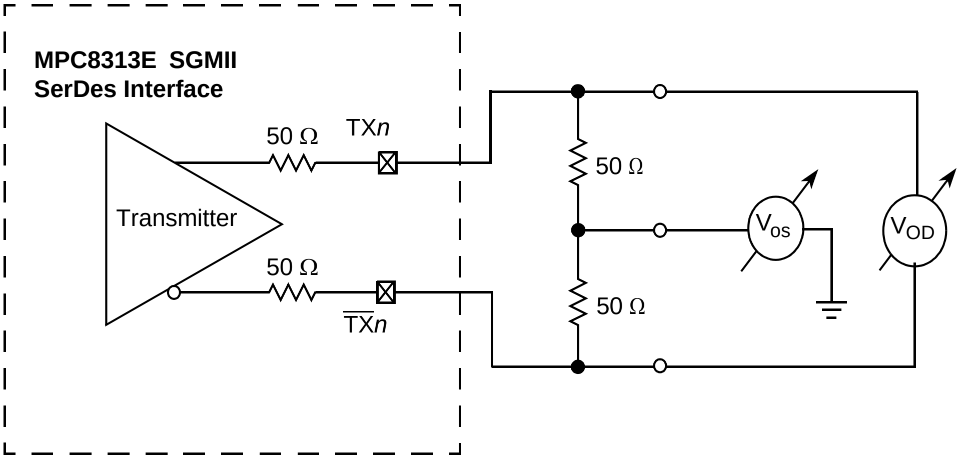


Figure 16. SGMII Transmitter DC Measurement Circuit

Table 33. SGMII DC Receiver Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	$XCOREV_{DD}$	0.95	1.0	1.05	V	
DC Input voltage range			N/A			1
Input differential voltage	$V_{RX\_DIFFp-p}$	100	—	1200	mV	2
Loss of signal threshold	VL_{OS}	30	—	100	mV	
Input AC common mode voltage	V_{CM_ACp-p}	—	—	100	mV	3
Receiver differential input impedance	Z_{RX_DIFF}	80	100	120	Ω	
Receiver common mode input impedance	Z_{RX_CM}	20	—	35	Ω	

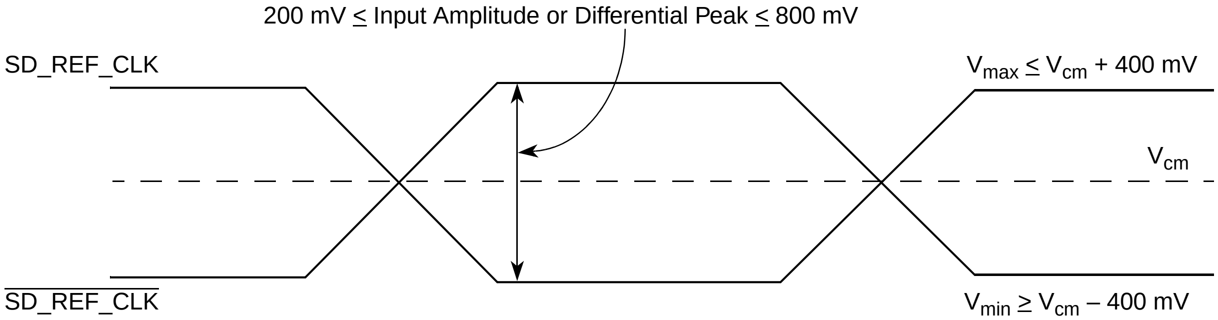


Figure 25. Differential Reference Clock Input DC Requirements (External AC-Coupled)

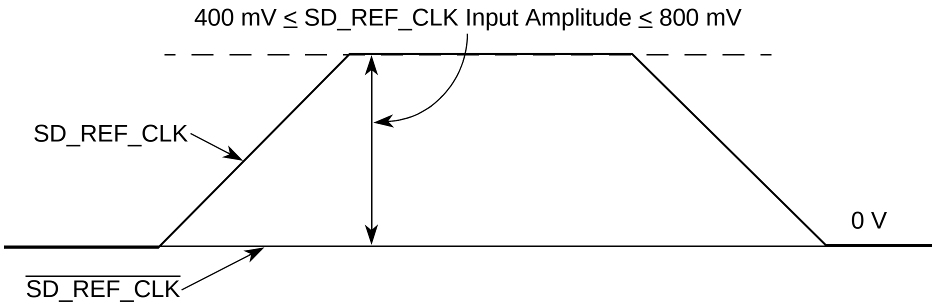


Figure 26. Single-Ended Reference Clock Input DC Requirements

9.2.3 Interfacing With Other Differential Signaling Levels

- With on-chip termination to $\text{XCOREV}_{\text{SS}}$, the differential reference clocks inputs are HCSL (high-speed current steering logic) compatible DC coupled.
- Many other low voltage differential type outputs like LVDS (low voltage differential signaling) can be used but may need to be AC coupled due to the limited common mode input range allowed (100 to 400 mV) for DC-coupled connection.
- LVPECL outputs can produce a signal with too large of an amplitude and may need to be DC-biased at the clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC coupling.

NOTE

Figure 27 through Figure 30 are for conceptual reference only. Due to the fact that the clock driver chip's internal structure, output impedance, and termination requirements are different between various clock driver chip manufacturers, it is possible that the clock circuit reference designs provided by clock driver chip vendors are different from what is shown in the figures. They might also vary from one vendor to the other. Therefore, Freescale can neither provide the optimal clock driver reference circuits, nor guarantee the correctness of the following clock driver connection reference circuits. It is recommended that the system designer contact the selected clock driver chip vendor for the optimal reference circuits for the MPC8313E SerDes reference clock receiver requirement provided in this document.

Table 47. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)[1] (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Note
JTAG external clock to output high impedance: Boundary-scan data TDO	t_{JTKLDZ} t_{JTKLOZ}	2 2	19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 34). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

This figure provides the AC test load for TDO and the boundary-scan outputs.

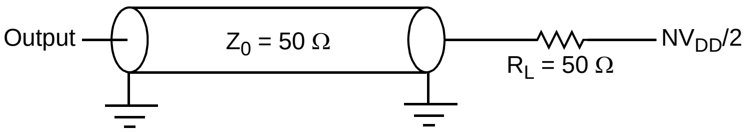
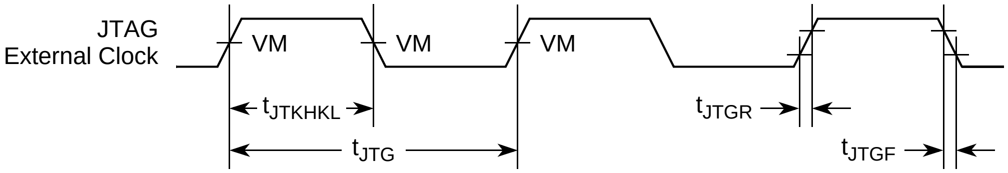


Figure 41. AC Test Load for the JTAG Interface

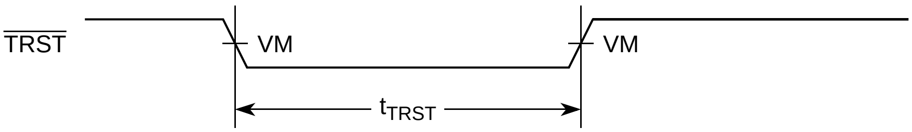
This figure provides the JTAG clock input timing diagram.



VM = Midpoint Voltage (NV_{DD}/2)

Figure 42. JTAG Clock Input Timing Diagram

This figure provides the $\overline{\text{TRST}}$ timing diagram.



VM = Midpoint Voltage (NV_{DD}/2)

Figure 43. $\overline{\text{TRST}}$ Timing Diagram

Table 51. PCI AC Timing Specifications at 66 MHz (continued)

Parameter	Symbol[1]	Min	Max	Unit	Note
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0	—	ns	2, 4

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

This table shows the PCI AC timing specifications at 33 MHz.

Table 52. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol[1]	Min	Max	Unit	Note
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0	—	ns	2, 4

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

This figure provides the AC test load for PCI.

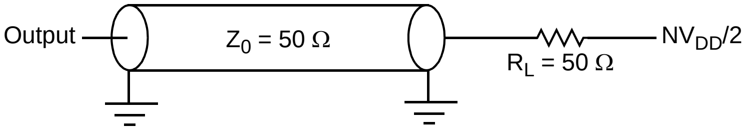


Figure 48. PCI AC Test Load

This figure shows the SPI timing in slave mode (external clock).

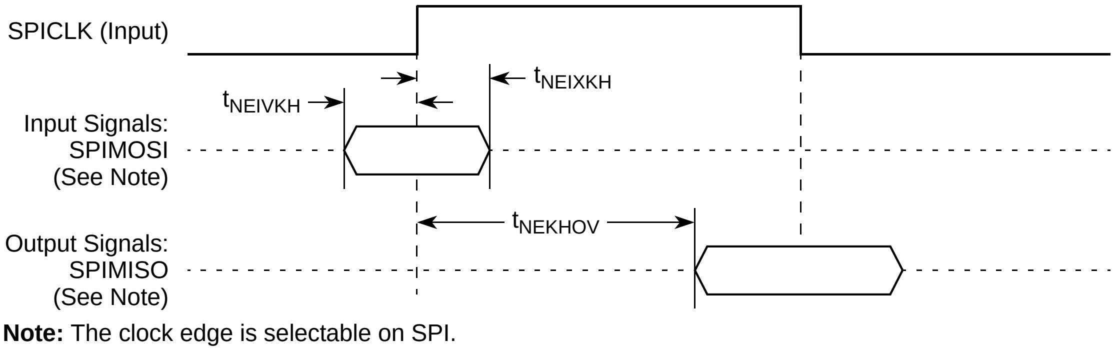


Figure 54. SPI AC Timing in Slave Mode (External Clock) Diagram

This figure shows the SPI timing in master mode (internal clock).

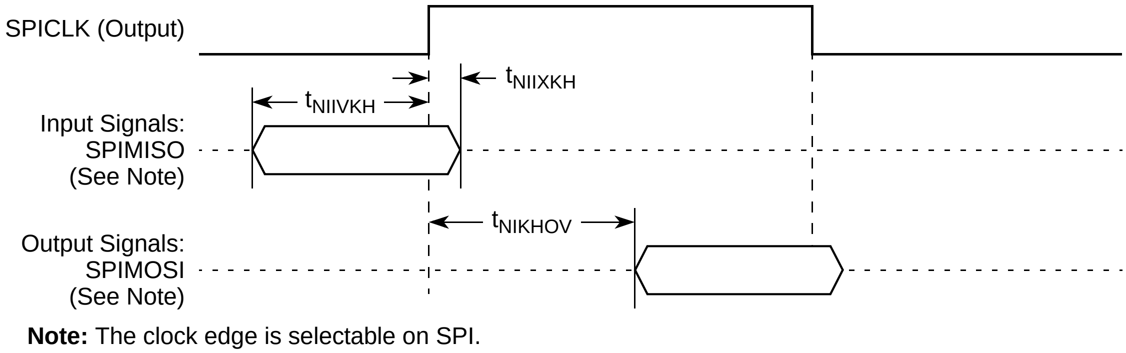


Figure 55. SPI AC Timing in Master Mode (Internal Clock) Diagram

19 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8313E is available in a thermally enhanced plastic ball grid array (TEPBGAII), see Section 19.1, “Package Parameters for the MPC8313E TEPBGAII,” and Section 19.2, “Mechanical Dimensions of the MPC8313E TEPBGAII,” for information on the TEPBGAII.

19.1 Package Parameters for the MPC8313E TEPBGAII

The package parameters are as provided in the following list. The package type is 27 mm × 27 mm, 516 TEPBGAII.

Package outline	27 mm × 27 mm
Interconnects	516
Pitch	1.00 mm
Module height (typical)	2.25 mm
Solder Balls	96.5 Sn/3.5 Ag(VR package) , 62 Sn/36 Pb/2 Ag (ZQ package) Ball diameter (typical)
0.6 mm	

Table 62. MPC8313E TEPBGAII Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
$\overline{\text{MEMC\_MCS0}}$	D10	O	GV_{DD}	—
$\overline{\text{MEMC\_MCS1}}$	A10	O	GV_{DD}	—
MEMC_MCKE	B14	O	GV_{DD}	3
MEMC_MCK	A13	O	GV_{DD}	—
$\overline{\text{MEMC\_MCK}}$	A14	O	GV_{DD}	—
MEMC_MODT0	B23	O	GV_{DD}	—
MEMC_MODT1	C23	O	GV_{DD}	—
Local Bus Controller Interface				
LAD0	K25	I/O	LV_{DD}	11
LAD1	K24	I/O	LV_{DD}	11
LAD2	K23	I/O	LV_{DD}	11
LAD3	K22	I/O	LV_{DD}	11
LAD4	J25	I/O	LV_{DD}	11
LAD5	J24	I/O	LV_{DD}	11
LAD6	J23	I/O	LV_{DD}	11
LAD7	J22	I/O	LV_{DD}	11
LAD8	H24	I/O	LV_{DD}	11
LAD9	F26	I/O	LV_{DD}	11
LAD10	G24	I/O	LV_{DD}	11
LAD11	F25	I/O	LV_{DD}	11
LAD12	E25	I/O	LV_{DD}	11
LAD13	F24	I/O	LV_{DD}	11
LAD14	G22	I/O	LV_{DD}	11
LAD15	F23	I/O	LV_{DD}	11
LA16	AC25	O	LV_{DD}	11
LA17	AC26	O	LV_{DD}	11
LA18	AB22	O	LV_{DD}	11
LA19	AB23	O	LV_{DD}	11
LA20	AB24	O	LV_{DD}	11
LA21	AB25	O	LV_{DD}	11
LA22	AB26	O	LV_{DD}	11
LA23	E22	O	LV_{DD}	11

Table 62. MPC8313E TEPBGAII Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
TSEC1_TXD1/TSEC_1588_PP2	AD6	O	LV$_{DDB}$	—
TSEC1_TXD0/USBDR_STP/TSEC_1588_PP3	AD5	O	LV$_{DDB}$	—
TSEC1_TX_EN/TSEC_1588_ALARM1	AB7	O	LV$_{DDB}$	—
TSEC1_TX_ER/TSEC_1588_ALARM2	AB8	O	LV$_{DDB}$	—
TSEC1_GTX_CLK125	AE1	I	LV$_{DDB}$	—
TSEC1_MDC/LB_POR_CFG_BOOT_ECC_DIS	AF6	O	NV$_{DD}$	9, 11
TSEC1_MDIO	AB9	I/O	NV$_{DD}$	—
ETSEC2				
TSEC2_COL/GTM1_TIN4/GTM2_TIN3/GPIO15	AB4	I/O	LV$_{DDA}$	—
TSEC2_CRS/$\overline{\text{GTM1\_TGATE4}}$/$\overline{\text{GTM2\_TGATE3}}$/GPIO16	AB3	I/O	LV$_{DDA}$	—
TSEC2_GTX_CLK/$\overline{\text{GTM1\_TOUT4}}$/$\overline{\text{GTM2\_TOUT3}}$/GPIO17	AC1	I/O	LV$_{DDA}$	12
TSEC2_RX_CLK/GTM1_TIN2/GTM2_TIN1/GPIO18	AC2	I/O	LV$_{DDA}$	—
TSCE2_RX_DV/$\overline{\text{GTM1\_TGATE2}}$/$\overline{\text{GTM2\_TGATE1}}$/GPIO19	AA3	I/O	LV$_{DDA}$	—
TSEC2_RXD3/GPIO20	Y5	I/O	LV$_{DDA}$	—
TSEC2_RXD2/GPIO21	AA4	I/O	LV$_{DDA}$	—
TSEC2_RXD1/GPIO22	AB2	I/O	LV$_{DDA}$	—
TSEC2_RXD0/GPIO23	AA5	I/O	LV$_{DDA}$	—
TSEC2_RX_ER/$\overline{\text{GTM1\_TOUT2}}$/$\overline{\text{GTM2\_TOUT1}}$/GPIO24	AA2	I/O	LV$_{DDA}$	—
TSEC2_TX_CLK/GPIO25	AB1	I/O	LV$_{DDA}$	—
TSEC2_TXD3/CFG_RESET_SOURCE0	W3	I/O	LV$_{DDA}$	—
TSEC2_TXD2/CFG_RESET_SOURCE1	Y1	I/O	LV$_{DDA}$	—
TSEC2_TXD1/CFG_RESET_SOURCE2	W5	I/O	LV$_{DDA}$	—
TSEC2_TXD0/CFG_RESET_SOURCE3	Y3	I/O	LV$_{DDA}$	—
TSEC2_TX_EN/GPIO26	AA1	I/O	LV$_{DDA}$	—
TSEC2_TX_ER/GPIO27	W1	I/O	LV$_{DDA}$	—
SGMII PHY				
TXA	U3	O		—
$\overline{\text{TXA}}$	V3	O		—
RXA	U1	I		—
$\overline{\text{RXA}}$	V1	I		—
TXB	P4	O		—
$\overline{\text{TXB}}$	N4	O		—

Table 62. MPC8313E TEPBGAII Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
RXB	R1	I		—
$\overline{\text{RXB}}$	P1	I		—
SD_IMP_CAL_RX	V5	I		200 Ω ± 10% to GND
$\overline{\text{SD\_REF\_CLK}}$	T5	I		—
SD_REF_CLK	T4	I		—
SD_PLL_TPD	T2	O		—
SD_IMP_CAL_TX	N5	I		100 Ω ± 10% to GND
SDAVDD	R5	I/O		—
SD_PLL_TPA_ANA	R4	O		—
SDAVSS	R3	I/O		—
USB PHY				
USB_DP	P26	I/O		—
USB_DM	N26	I/O		—
USB_VBUS	P24	I/O		—
USB_TPA	L26	I/O		—
USB_RBIAS	M24	I/O		—
USB_PLL_PWR3	M26	I/O		—
USB_PLL_GND	N24	I/O		—
USB_PLL_PWR1	N25	I/O		—
USB_VSSA_BIAS	M25	I/O		—
USB_VDDA_BIAS	M22	I/O		—
USB_VSSA	N22	I/O		—
USB_VDDA	P22	I/O		—
GTM/USB				
USBDR_DRIVE_VBUS/GTM1_TIN1/GTM2_TIN2/LSRCID0	AD23	I/O	NV_{DD}	—
USBDR_PWRFAULT/$\overline{\text{GTM1\_TGATE1}}$/$\overline{\text{GTM2\_TGATE2}}$/ LSRCID1	AE23	I/O	NV_{DD}	—
USBDR_PCTL0/$\overline{\text{GTM1\_TOUT1}}$/LSRCID2	AC22	O	NV_{DD}	—
USBDR_PCTL1/LBC_PM_REF_10/LSRCID3	AB21	O	NV_{DD}	—

Table 65. System PLL Multiplication Factors (continued)

RCWL[SPMF]	System PLL Multiplication Factor
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

Note:

1. If RCWL[DDRCM] and RCWL[LBCM] are both cleared, the system PLL VCO frequency = (CSB frequency) × (System PLL VCO Divider).
2. If either RCWL[DDRCM] or RCWL[LBCM] are set, the system PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO Divider).
3. The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 450–750 MHz

As described in Section 20, “Clocking,” the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (SYS_CLK_IN or PCI_SYNC_IN) and the internal coherent system bus clock (*csb_clk*). This table shows the expected frequency values for the CSB frequency for select *csb_clk* to SYS_CLK_IN/PCI_SYNC_IN ratios.

Table 66. CSB Frequency Options

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* :Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			24	25	33.33	66.67
			csb_clk Frequency (MHz)			
High	0010	2:1				133
High	0011	3:1			100	
High	0100	4:1		100	133	
High	0101	5:1	120	125	167	
High	0110	6:1	144	150		
Low	0010	2:1				133
Low	0011	3:1			100	
Low	0100	4:11		100	133	
Low	0101	5:1	120	125	167	
Low	0110	6:1	144	150		

[1] CFG_CLKIN_DIV select the ratio between SYS_CLK_IN and PCI_SYNC_OUT.

[2] SYS_CLK_IN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

Table 69. Package Thermal Characteristics for TEPBGAII (continued)

Characteristic	Board Type	Symbol	TEPBGA II	Unit	Note
Junction-to-case	—	$R_{\theta JC}$	8	°C/W	5
Junction-to-package top	Natural convection	Ψ_{JT}	7	°C/W	6

Note:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

21.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$, where $P_{I/O}$ is the power dissipation of the I/O drivers.

21.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)
T_A = ambient temperature for the package (°C)
$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

21.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter